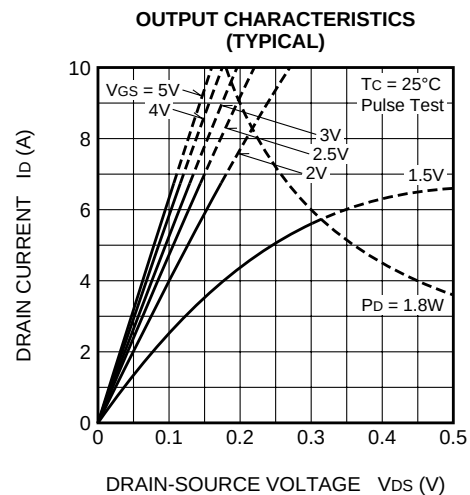
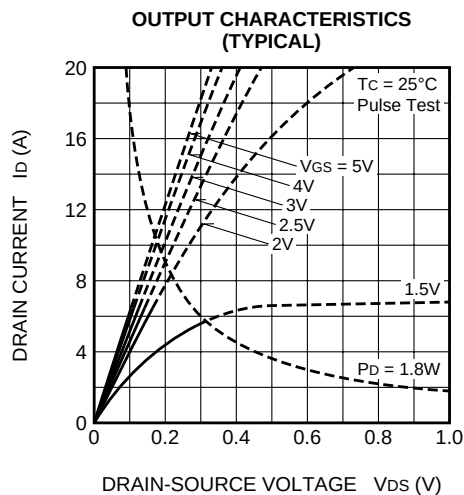
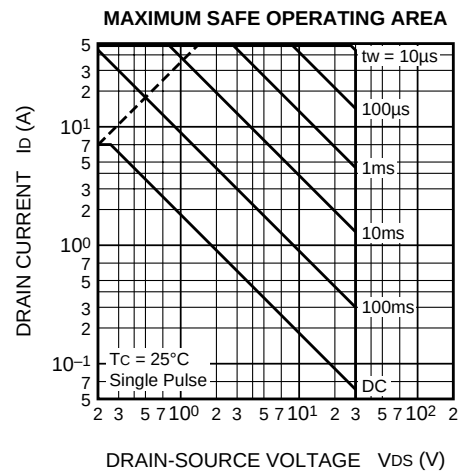
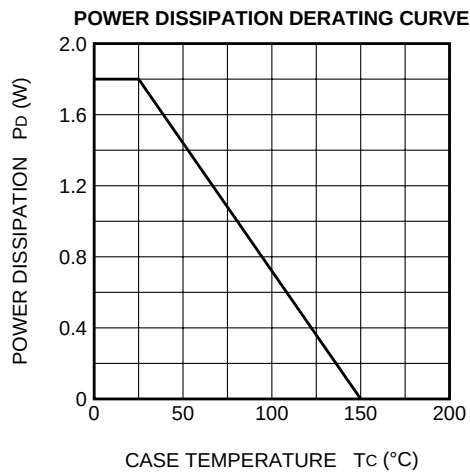
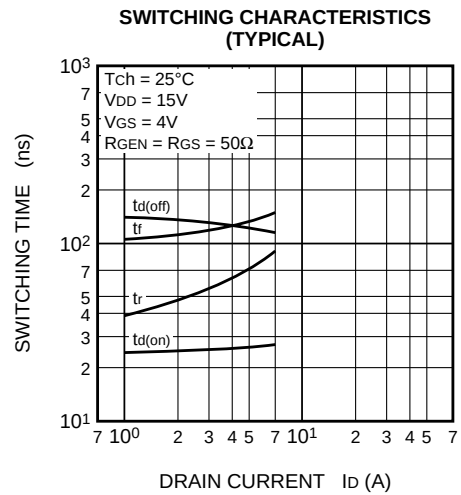
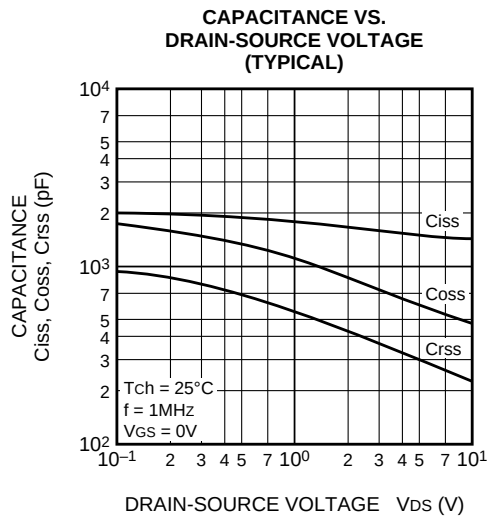
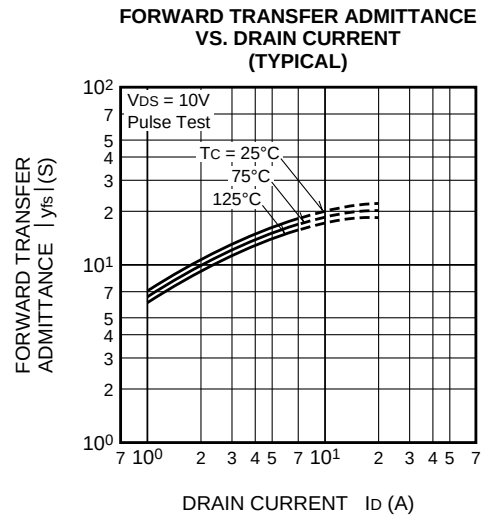
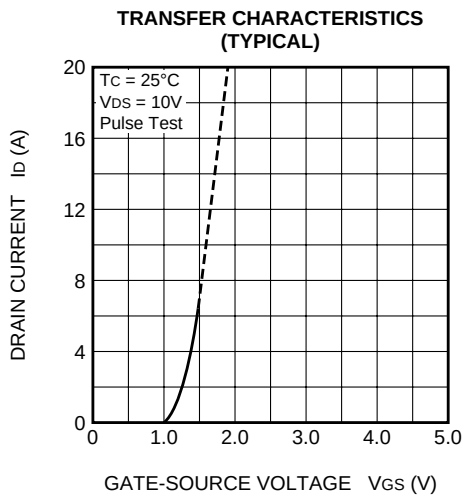
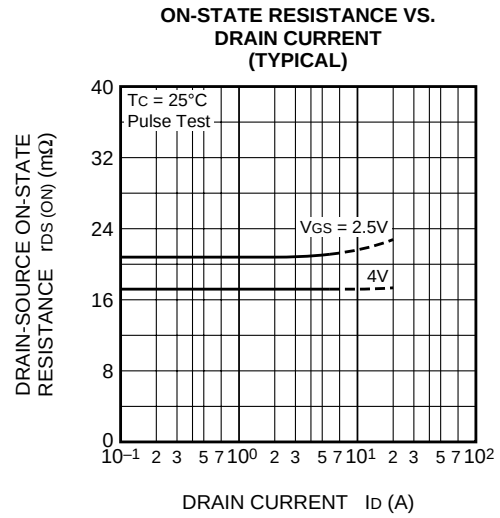
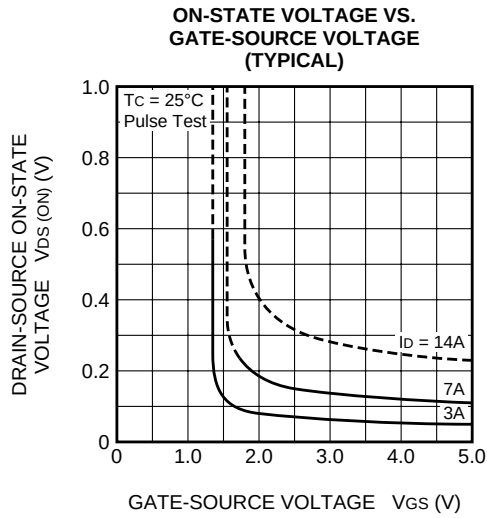


ELECTRICAL CHARACTERISTICS (Tch = 25°C)

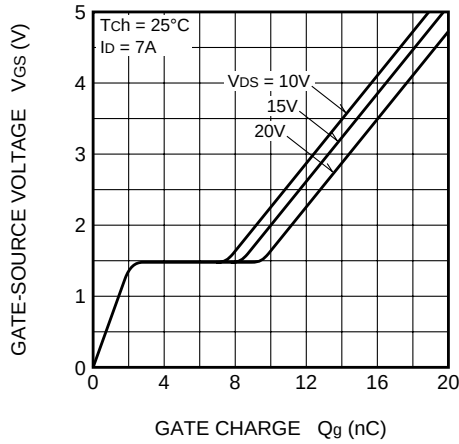
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	30	—	—	V
IGSS	Gate-source leakage current	VGS = ±10V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = 20V, VGS = 0V	—	—	0.1	mA
VGS(th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	0.5	0.9	1.3	V
rDS(ON)	Drain-source on-state resistance	Id = 7A, VGS = 4V	—	20	26	mΩ
rDS(ON)	Drain-source on-state resistance	Id = 3A, VGS = 2.5V	—	28	38	mΩ
VDS(ON)	Drain-source on-state voltage	Id = 7A, VGS = 4V	—	0.14	0.18	V
yfs	Forward transfer admittance	Id = 7A, VDS = 10V	—	18	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	1450	—	pF
Coss	Output capacitance		—	480	—	pF
Crss	Reverse transfer capacitance		—	230	—	pF
td(on)	Turn-on delay time	VDD = 10V, Id = 3A, VGS = 4V, RGEN = RGS = 50Ω	—	25	—	ns
tr	Rise time		—	55	—	ns
td(off)	Turn-off delay time		—	130	—	ns
tf	Fall time		—	120	—	ns
VSD	Source-drain voltage	IS = 1.7A, VGS = 0V	—	0.75	1.1	V
Rth(ch-a)	Thermal resistance	Channel to ambient	—	—	69.4	°C/W
trr	Reverse recovery time	IS = 1.7A, dis/dt = -50A/μs	—	100	—	ns

PERFORMANCE CURVES

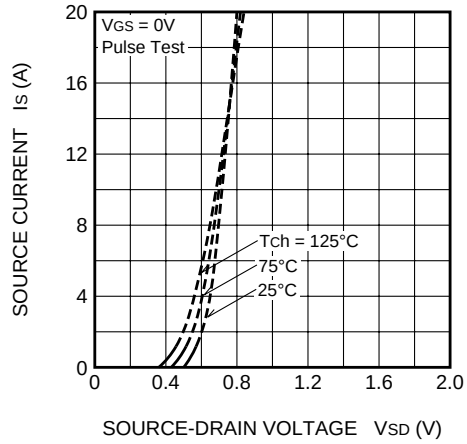




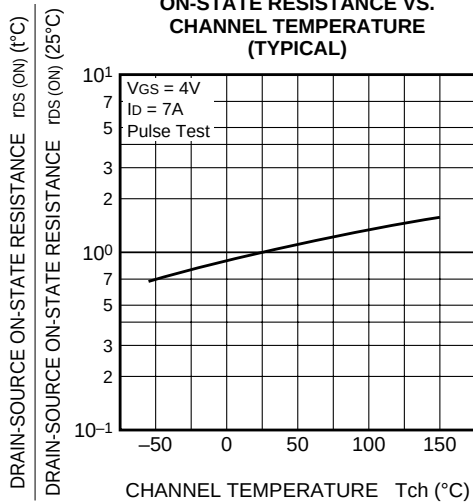
GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)



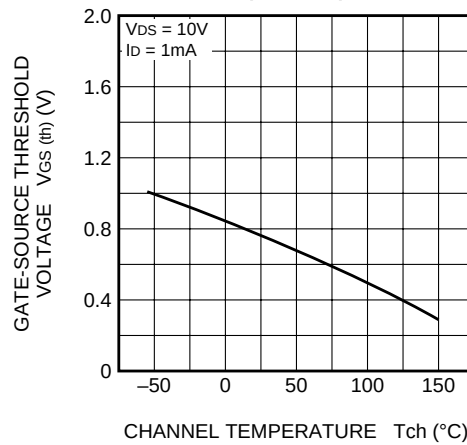
SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



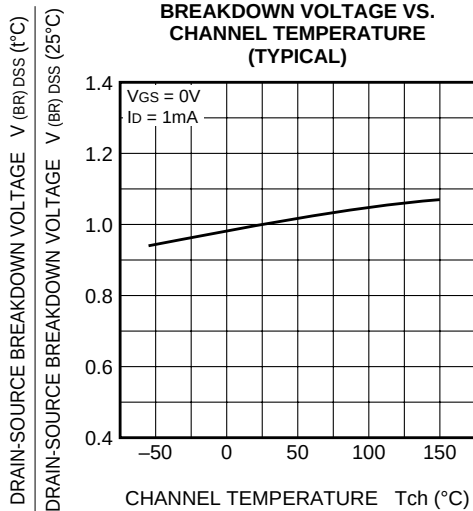
ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)



THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS

